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The invention relates to photodetectors on the semiconductors base, in particular, to photodetectors of ultra-violet radiation and can be used in the optoelectronic systems for determining the intensity and dose of ultra-violet radiation emitted by the Sun and other sources.

In the structure of the photodetector of ultra-violet radiation with a superficial potential barrier formed of semiconductors A^3B^5 with the prohibited power width E_{g1} , solid solutions thereof with the prohibited power width E_{g2} and SnO_2 or ITO, in the semiconductors A^3B^5 at a surface distance less than the absorption length of the visible radiation it is formed an isotype heterojunction between the semiconductors A^3B^5 and solid solutions thereof with the prohibited power width $E_{g2} > E_{g1}$.

The technical result consists in manufacturing of a photodetector sensitive solely to the ultra-violet radiation.

Claims: 1

Fig.: 1